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AMENDMENTS TO THE CLAIMS:

Please cancel claims 1-3 and 31-36, without prejudice or disclaimer and amend the claims as follows:

1. - 20. (Canceled)

21. (Previously presented) A semiconductor laser diode chip with an active layer mounted on a substrate, comprising:
a first pair of marks formed in the vicinity of said active layer and straddling said active layer; and
a second pair of marks straddling said active layer, said second pair of marks located at a further distance from said active layer than said first pair of marks,
wherein said second pair of marks align with a pair of substrate side marks formed at a position opposed to said second pair of marks, and
wherein said first pair of marks comprises lines formed on an upper portion of said active layer.

22. (Previously presented) The semiconductor laser diode chip, as claimed in claim 21, wherein said first pair of marks comprises thin lines formed parallel to said active layer.

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23. (Previously presented) The semiconductor laser diode chip, as claimed in claim 22,
wherein said first pair of marks comprises a metallic film.

24. - 25. (Canceled)

26. (Previously presented) A semiconductor laser diode chip with an active layer
mounted on a substrate, comprising:

a first pair of marks formed in the vicinity of said active layer and straddling said
active layer; and
style="padding-left: 40px;">a second pair of marks straddling said active layer, said second pair of marks located
at a further distance from said active layer than said first pair of marks,
wherein said second pair of marks align with a pair of substrate side marks formed at
a position opposed to said second pair of marks,
wherein said first pair of marks comprises lines formed on an upper portion of said
active layer, and
wherein said second pair of marks have a circular shape.

27. (Previously presented) The semiconductor laser diode chip, as claimed in claim 21,
wherein said pair of substrate side marks have a diameter different than a diameter of said
second pair of marks.

28. (Previously presented) The semiconductor laser diode chip, as claimed in claim 21,
wherein a distance between each individual mark of said first pair of marks is 10 μm .

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29. (Previously presented) An optical module, comprising:
 - a substrate; and
 - the semiconductor laser diode chip of claim 1 formed on the substrate.
30. (Previously presented) The module of claim 29, further comprising:
 - an optical fiber arranged on the substrate and connected to the semiconductor laser diode chip.
31. - 36. (Canceled)